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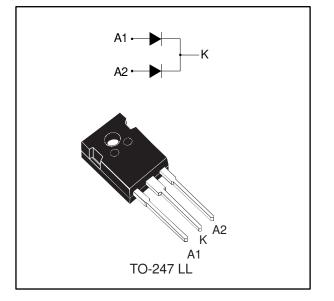
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1200 V power Schottky silicon carbide diode

Datasheet - production data



Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Robust high voltage periphery
- Operating T_j from -40 °C to 175 °C
- ECOPACK[®]2 compliant

Description

The SiC diode, available in TO-247 LL, is an ultrahigh performance power Schottky rectifier. It is manufactured using a silicon carbide substrate. The wide band-gap material allows the design of a low V_F Schottky diode structure with a 1200 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC and secondary side applications, this ST SiC diode will boost the performance in hard switching conditions. This rectifier will enhance the performance of the targeted application. Its high forward surge capability ensures a good robustness during transient phases.

Table 1: Device summary

Symbol	Value
I _{F(AV)}	2 x 15 A
V _{RRM}	1200 V
T _j (max.)	175 °C
V _F (typ.)	1.35 V

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This is information on a product in full production.

1 Characteristics

Table 2: Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol		Parameter		Value	Unit	
VRRM	Repetitive peak reverse vo	Repetitive peak reverse voltage (T _j = -40 °C to +175 °C)				
I _{F(RMS)}	Forward rms current			38	А	
		T _C = 150 °C DC current		15/30		
IF(AV)	I _{F(AV)} Average forward current	T _C = 135 °C DC current	Per diode/per device	21/42	А	
		T _C = 25 °C DC current		38/76		
IFRM	Repetitive peak forward current	$T_{C} = 150 \ ^{\circ}C, T_{j} = 175 \ ^{\circ}C, \delta = 0.1$		61	А	
		t _p = 10 ms	Tc = 25 °C	105		
IFSM	Surge non repetitive	sinusoidal	T _C = 150 °C	90	А	
1 310	forward current	t _p = 10 μs square	T _C = 25 °C	630		
T _{stg}	Storage temperature range	9		-65 to +175	°C	
Tj	Operating junction tempera	ature range		-40 to +175	°C	

Table 3: Thermal resistance parameters

	Symbol	Parameter		Typ. value	Max. value	Unit
	R _{th(j-c)} Junction to case	lupation to appa	Per diode	0.50	0.70	0 0 AN
		Junction to case	Per device	0.25	0.35	°C/W

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	Vr = Vrrm	-	7.5	90	μA
IR ⁽ ⁷		T _j = 150 °C		-	45	600	
$M_{-}(2)$	Forward voltage drop	T _j = 25 °C	– I _F = 15 A	-	1.35	1.50	V
V _F ⁽²⁾		T _j = 150 °C		-	1.75	2.25	

Notes:

 $^{(1)}$ Pulse test: tp = 10 ms, δ < 2% $^{(2)}$ Pulse test: tp = 500 µs, δ < 2%

To evaluate the conduction losses, use the following equation:

 $P = 1.09 \ x \ I_{F(AV)} + 0.0775 \ x \ I_{F^2(RMS)}$



Characteristics

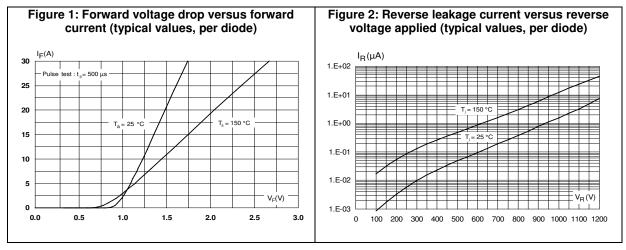
1120							
	Table 5: Dynamic electrical characteristics (per diode)						
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
Q _{Cj} ⁽¹⁾	Total capacitive charge	V _R = 800 V	-	94	-	nC	
0	Total consoitance	$V_R = 0 V$, $T_c = 25 °C$, $F = 1 MHz$	-	1200	-	<u>~</u> ۲	
Cj	Total capacitance	V_R = 800 V, T_c = 25 °C, F = 1 MHz	-	78	-	pF	

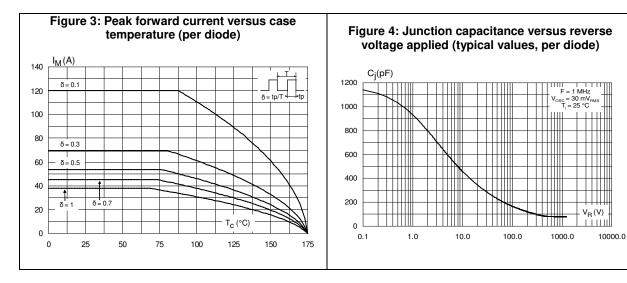
Notes:

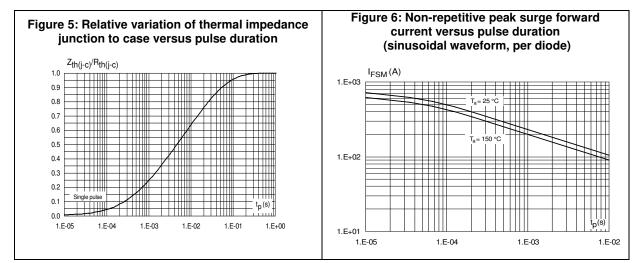
⁽¹⁾Most accurate value for the capacitive charge: $Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$



1.1 Characteristics (curves)



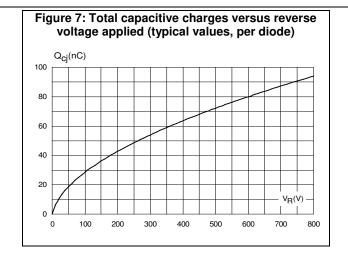




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Characteristics





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2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.9 to 1.2 N m

2.1 TO-247 long leads package information

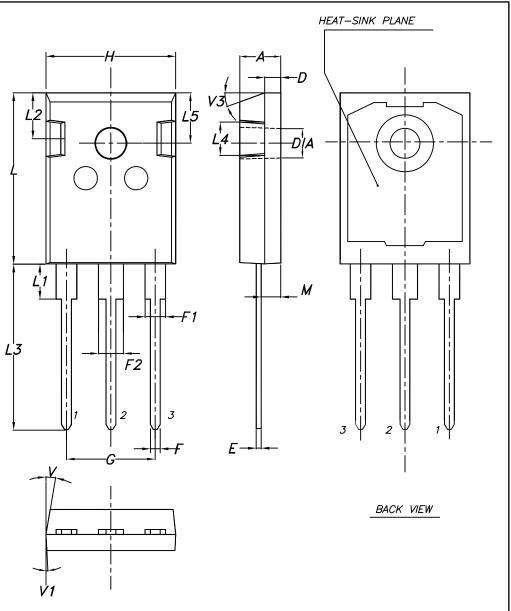


Figure 8: TO-247 long leads package outline

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Package information

112C					Package	information	
Table 6: TO-247 long leads package mechanical data							
Dim.		mm.			Inches		
Dim.	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	4.90		5.15	0.192		0.202	
D	1.85		2.10	0.072		0.082	
E	0.55		0.67	0.021		0.026	
F	1.07		1.32	0.042		0.051	
F1	1.90		2.38	0.074		0.093	
F2	2.87		3.38	0.110		0.133	
G		10.90 BSC		0.429 BSC			
Н	15.77		16.02	0.620		0.630	
L	20.82		21.07	0.810		0.820	
L1	4.16		4.47	0.163		0.175	
L2	5.49		5.74	0.216		0.225	
L3	20.05		20.30	0.789		0.799	
L4	3.68		3.93	0.144		0.154	
L5	6.04		6.29	0.237		0.247	
М	2.25		2.55	0.088		0.100	
V		10°			10°		
V1		3°			3°		
V3		20°			20°		
DIA	3.55		3.66	0.139		0.143	

3 Ordering information

Table 7: Ordering information						
Order code	Marking	Package	Weight	Base qty.	Delivery mode	
STPSC30H12CWL	STPSC30H12CWL	TO-247 LL	6.09 g	30	Tube	

4 Revision history

Table 8: Document revision histor

Date	Revision	Changes
15-Feb-2017	1	Initial release.



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